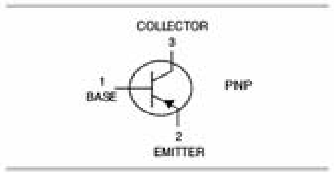
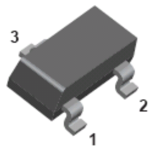
PNP hige-voltage transistor BSS63

FEATURES

- Low current (max. 100 mA)
- High voltage (max. 100 V).

Lead-free





SOT-23

APPLICATIONS

- High-voltage general purpose
- Switching applications.

ORDERING INFORMATION

Type No.	Marking	Package Code
BSS63	BM	SOT-23

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-110	V
V_{CEO}	Collector-Emitter Voltage	-110	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current DC	-100	mA
I_{CM}	peak collector current	-100	mA
I_{BM}	peak base current	-100	mA
P_{tot}	Collector power dissipation $T_{amb} \leq 25$ ℃	250	mW
T_{stg}	Storage Temperature	-55 to +150	℃
T_j	Junction Temperature	150	℃
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	500	K/W

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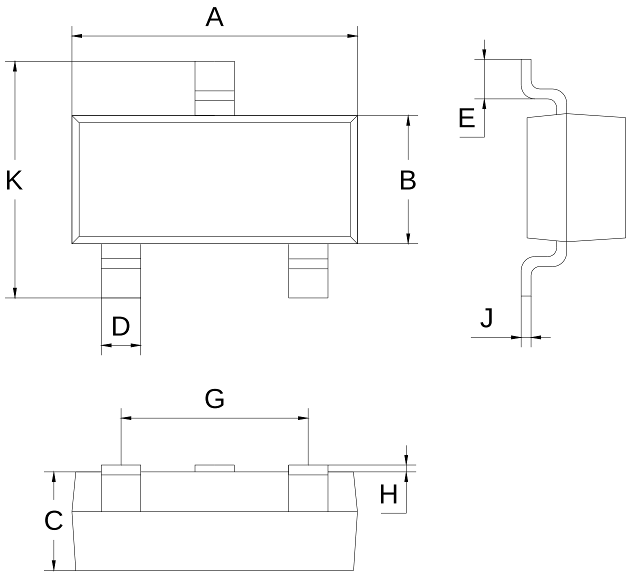
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	V_{CB}=-90V I_E=0			-100	nA
Emitter cut-off current	I_{EBO}	V_{EB}=-6V,I_C=0			-100	nA
DC current gain	h_{FE}	V_{CE}=-1V I_C=-10mA	30			
		V_{CE}=-1V I_C=-25mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-25mA I_B=-2.5mA			-250	mV
base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-25mA I_B=-2.5mA			-900	mV
Transition frequency	f_T	V_{CE}=-5V,I_C=-25mA, f=100MHz	50	85		MHz
Collector Capacitance	C_c	I_E = i_e = 0; V_{CB} = –10 V; f = 1 MHz		3		pF

PNP hige-voltage transistor BSS63

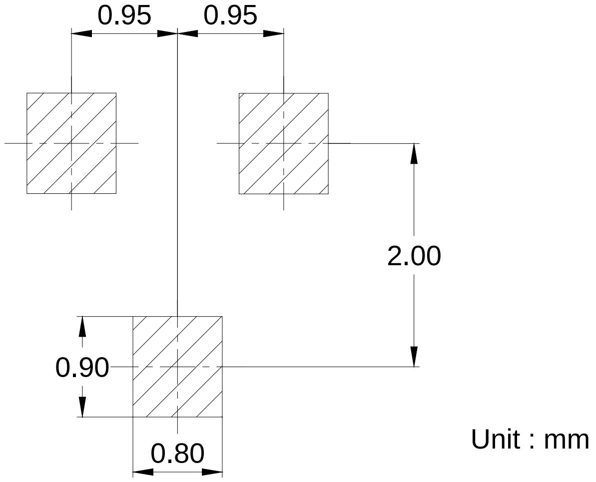
PACKAGE OUTLINE

Plastic surface mounted package SOT-23



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	1.0 Typical	
D	0.4 Typical	
E	0.35	0.48
G	1.80	2.00
H	0.02	0.1
J	0.1 Typical	
K	2.20	2.60
All Dimensions in mm		

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BSS63	SOT-23	3000/Tape&Reel